

E1
side surfaces of the poles and formed of an insulation material having a higher hardness than polyimide, and a second film of polyimide buried among said a plurality of poles with the first film formed on the side surfaces thereof.

3. (Twice Amended) A semiconductor light-emitting device having an electrode structure including a bonding pad formed on an insulation film without penetrating the insulation film, the insulation film being formed above a base substrate,

E2
the insulation film comprising a plurality of poles of polyimide, a first film formed on each side surfaces of the poles and formed of an insulation material having a higher hardness than polyimide, and a second film of polyimide buried among said a plurality of poles with the first film formed on side surfaces thereof.

E3
6. (Amended) A semiconductor light-emitting device according to claim 3, wherein the first film is also formed on upper surfaces of the second film.

E4
7. (Thrice Amended) A semiconductor light-emitting device according to claim 3, wherein a third film of an insulation material is sandwiched between the insulation film and the bonding pad.

E5
11. (Amended) A semiconductor light-emitting device according to claim 3, wherein the insulation film is formed on a layer formed on the base substrate, the layer being formed

of a material having a higher hardness than the polyimide.

13. (Thrice Amended) A semiconductor light-emitting device including a waveguide, a lower electrode formed below the waveguide, and an upper electrode formed above the waveguide, the upper electrode having an electrode structure, the electrode structure including a bonding pad formed on an insulation film without penetrating the insulation film, the insulation film being formed above a base substrate, the insulation film comprising a plurality of poles of polyimide, a first film formed on each side surfaces of the poles and formed of an insulation material having a higher hardness than polyimide, and a second film of polyimide buried among said a plurality of poles with the first film formed on the side surfaces thereof.

19. (New) An electrode structure according to claim 1, wherein the first film is also formed on upper surfaces of the poles.

20. (New) An electrode structure according to claim 1, wherein the first film is also formed on upper surfaces of the second film.

21. (New) A semiconductor light-emitting device according to claim 13, wherein the first film is also formed on upper surfaces of the poles.

Amendment under 37 CFR 1.111
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22. (New) A semiconductor light-emitting device according to claim 13, wherein
the first film is also formed on upper surfaces of the second film.
